

N-Channel Enhancement-Mode **Vertical DMOS FET**

Features

- Low threshold (1.0V max.)
- On-resistance guaranteed at V_{GS} = 2, 3, and 5V
- High input impedance
- Low input capacitance (130pF typical)
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

Applications

- Logic level interfaces
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package	Wafer / Die Options					
	TO-92	NW (Die in wafer form)	NJ (Die on adhesive tape)	ND (Die in waffle pack)			
TN0702	TN0702N3-G	TN5702NW	TN5702NJ	TN5702ND			

For packaged products, -G indicates package is RoHS compliant ('Green'). Devices in Wafer / Die form are RoHS compliant ('Green'). Refer to Die Specification VF57 for layout and dimensions.

Product Summary

Device	BV _{DSS} /BV _{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)	 _{D(ON)} (min) (A)	I _{D(ON)} (min) (A)
TN0702N3-G	20	1.3	0.5	1.0

Absolute Maximum Ratings

	•
Parameter	Value
Drain-to-source voltage	BV _{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configurations



Product Marking



TO-92 (N3)

Package may or may not include the following marks: Si or 👘



Thermal Characteristics

Package	I _D (continuous) [†] (mA)	I _D (pulsed) (A)	Power Dissipation @T _c = 25°C (W)	θ _{jc} (°C/W)	θ _{ja} (°C/W)	l _{DR} † (mA)	I _{DRM} (A)
TO-92	530	1.0	1.0	125	170	530	1.0

Notes:

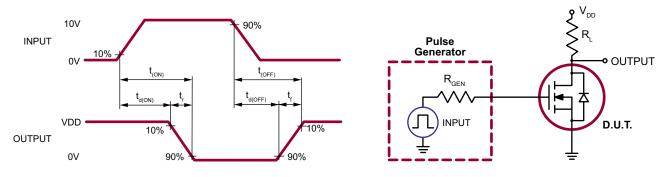
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions
BV _{DSS}	Drain-to-source breakdown voltage	20	-	-	V	$V_{GS} = 0V, I_{D} = 1.0 \text{mA}$
$V_{\rm GS(th)}$	Gate threshold voltage	0.5	0.8	1.0	V	$V_{GS} = V_{DS}$, $I_D = 1.0 \text{mA}$
$\Delta V_{GS(th)}$	Change in V _{GS(th)} with temperature	-	-	-4.0	mV/°C	$V_{GS} = V_{DS}$, $I_D = 1.0 \text{mA}$
I _{GSS}	Gate body leakage	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
		-	ı	100	nA	$V_{GS} = 0V, V_{DS} = Max Rating$
I _{DSS}	Zero gate voltage drain current	-	-	100	μA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$, $T_{A} = 125$ °C
I _{D(ON)}	On-state drain current	0.5	1.0	-	Α	$V_{GS} = V_{DS} = 5.0V$
	Static drain-to-source on-state resistance	-	4.0	5.0	Ω	$V_{GS} = 2.0V, I_{D} = 50mA$
R _{DS(ON)}		-	1.9	2.5		$V_{GS} = 3.0V, I_{D} = 200mA$
			1.0	1.3		$V_{GS} = 5.0V, I_{D} = 500mA$
$\Delta R_{DS(ON)}$	Change in R _{DS(ON)} with temperature	-	-	0.75	%/°C	$V_{GS} = 5.0V, I_{D} = 500mA$
G _{FS}	Forward transductance	100	500	-	mmho	$V_{DS} = 5.0V, I_{D} = 500mA$
C _{ISS}	Input capacitance	-	130	200		V _{GS} = 0V,
C _{oss}	Common source output capacitance	-	70	125	pF	$V_{DS} = 20V$
C _{RSS}	Reverse transfer capacitance	-	30	60		f = 1.0MHz
t _{d(ON)}	Turn-on delay time	-	ı	20		
t _r	Rise time	-	1	20	no	$V_{DD} = 20V$,
t _{d(OFF)}	Turn-off delay time	-	-	30	ns	$I_{D} = 0.5A,$ $R_{GEN} = 25\Omega$
t _f	Fall time	-	-	20		GLN
V _{SD}	Diode forward voltage drop	-	-	1.0	V	$V_{GS} = 0V, I_{SD} = 0.5A$

Notes:

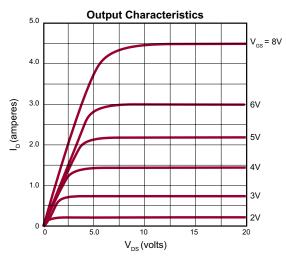
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

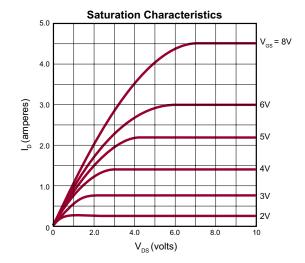
Switching Waveforms and Test Circuit

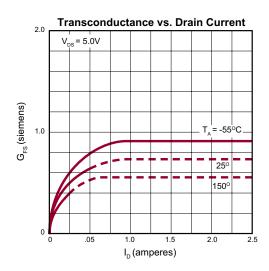


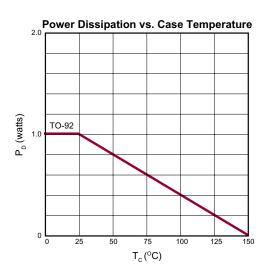
[†] I_D (continuous) is limited by max rated T_i .

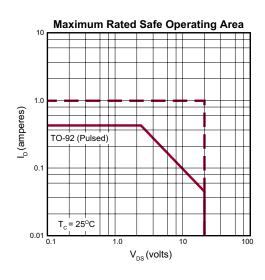
Typical Performance Curves

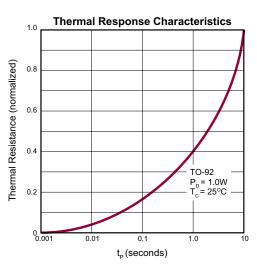




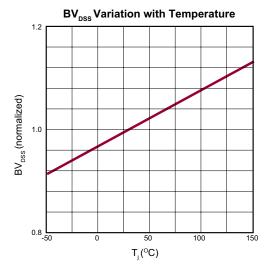


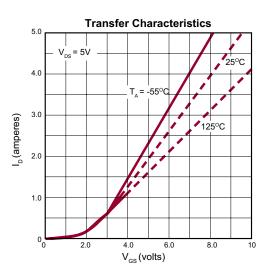


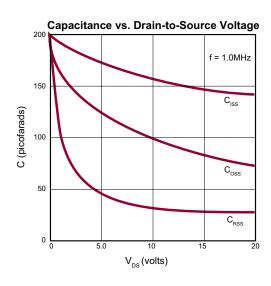


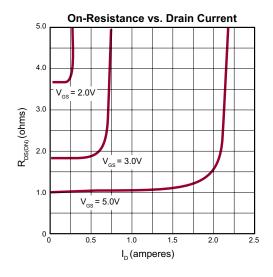


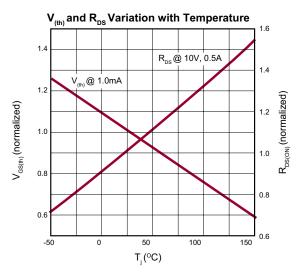
Typical Performance Curves (cont.)

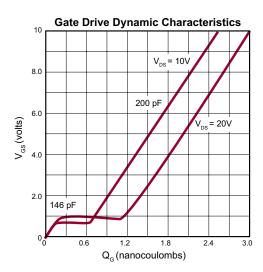




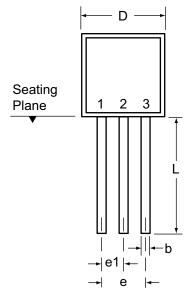


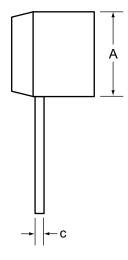






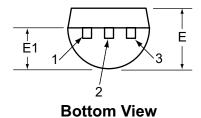
3-Lead TO-92 Package Outline (N3)





Front View

Side View



Symbol		Α	b	С	D	E	E1	е	e1	L
Dimensions (inches)	MIN	.170	.014 [†]	.014 [†]	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022 [†]	.022 [†]	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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^{*} This dimension is not specified in the JEDEC drawing.

[†] This dimension differs from the JEDEC drawing.